H3D10065L

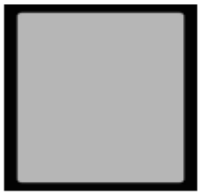
Silicon Carbide Schottky Diode Chip

V_{RRM}	=	650	V
$I_{F(AVG)}$	=	10	A
Q_C	=	25	nC

Features

- 650-Volt Schottky Rectifier
- Zero Reverse Recovery
- Zero Forward Recovery
- Positive Temperature Coefficient on V_F
- Temperature-Independent Switching Behavior

Chip Outline



Part Number	Die Size	Anode	Cathode
H3D10065L	1.94×1.94 mm^2	Al	Ni/Ag

Maximum Ratings

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	650	V		
V_{DC}	DC Blocking Voltage	650	V		
$I_{F(AVG)}$	Average Forward Current	10	A	$T_C \leq 153^{\circ}C$	1
I_{FSM}	Non-Repetitive Forward Surge Current	85	A	$T_C = 25^{\circ}C$, $t_p = 8.3ms$, Half Sine Wave	1
T_J	Operating Junction Temperature	-55 to 175	$^{\circ}C$		

1. Assumes Thermal Resistance of 1.16°C/W or less

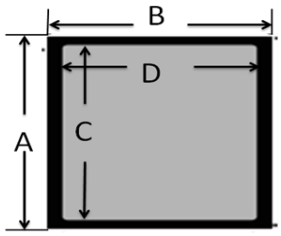
Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.4 1.75	1.65 2.3	V	I_F = 10A, T_J = 25°C I_F = 10A, T_J = 175°C	Fig.1
I_R	Reverse Current	1 5	20 100	μA	V_R = 650V, T_J = 25°C V_R = 650V, T_J = 175°C	Fig.2
C	Total Capacitance	440 57 46	/	pF	V_R = 1V, T_J = 25°C, f = 1MHz V_R = 200V, T_J = 25°C, f = 1MHz V_R = 400V, T_J = 25°C, f = 1MHz	Fig.3
Q_C	Total Capacitive Charge	25	/	nC	V_R = 650V, I_F = 10A di/dt = 200A/μs, T_J = 25°C	Fig.4

Mechanical Parameters

Parameter	Typ.	Unit
Die Size	1.94×1.94	mm^2
Anode Pad Opening	1.2×1.2	mm^2
Thickness	350±50	μm
Wafer Size	100	mm
Anode Metallization (Al)	4	μm
Cathode Metallization (Ni/Ag)	1.6	μm
Frontside Passivation	Polyimide	

Chip Dimensions



Symbol	Dimension
A	1.94mm
B	1.94mm
C	1.2mm
D	1.2mm

Typical Performance

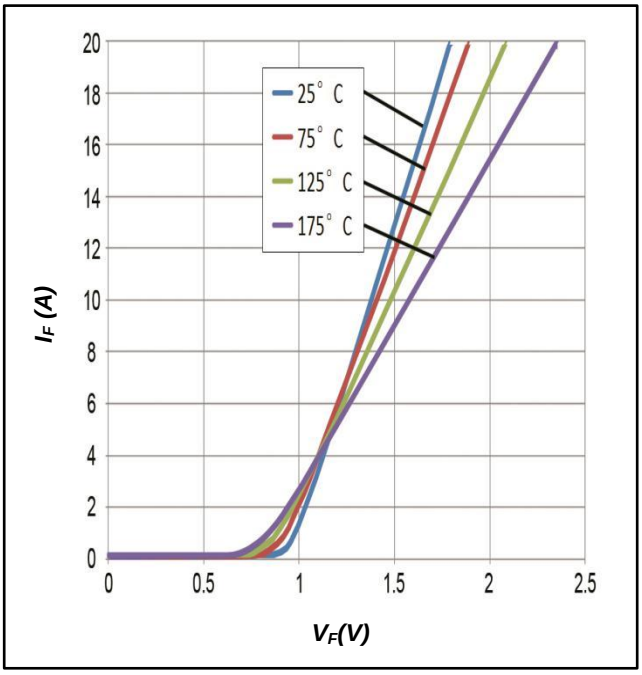


Figure 1. Forward Characteristics

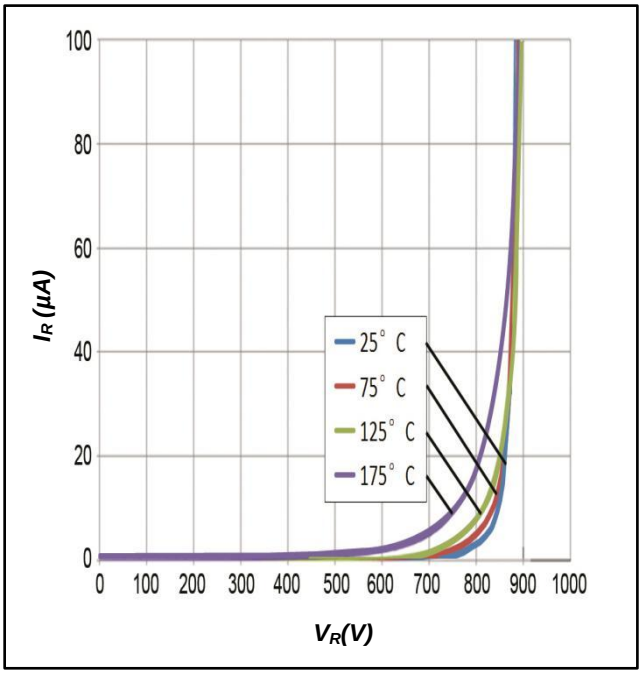


Figure 2. Reverse Characteristics

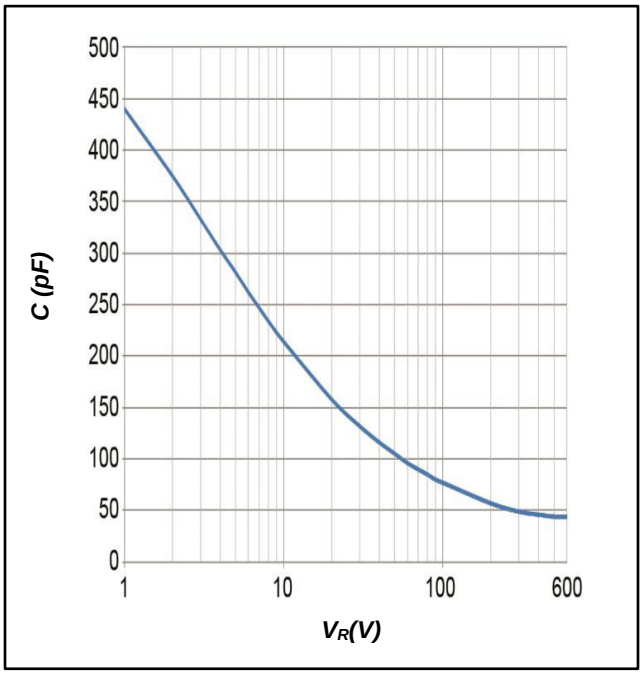


Figure 3. Total Capacitance vs. Reverse Voltage

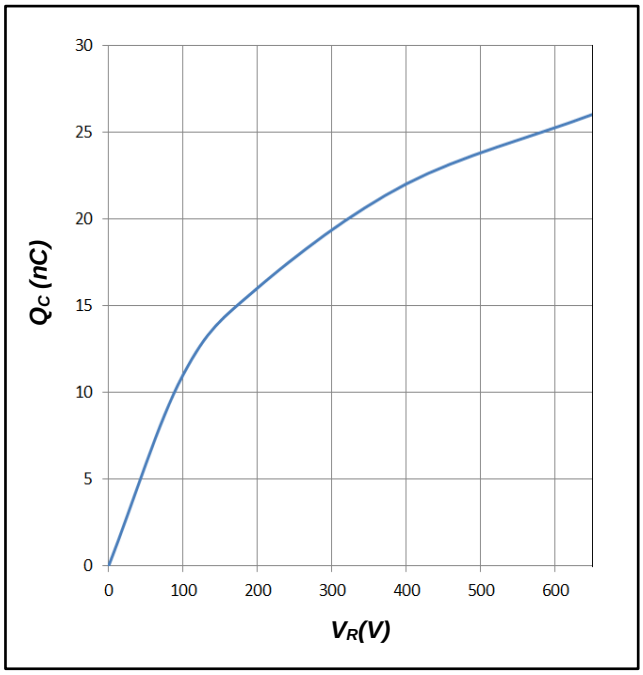


Figure 4. Total Capacitance Charge vs. Reverse Voltage